PCN Number:			20180223000			PCN Date:	F	February 26, 2018			
Title: Datasheet for			r OPA	338							
Customer Contact:			PCN Manager					Dept:		Quality Services	
Change Type:											
Assembly Site				Design				Wafer Bump Site			
Assembly Process				\boxtimes	Data Shee	et			Wafer	Bump Material	
Assembly Materials					Part numb	oer change			Wafer	Bump Process	
Mechanical Specification					Test Site				Wafer	Fab Site	
Packing/Shipping/Labeling				Test Proce	ess			Wafer	Fab Materials		
		·				•				Wafer	Fab Process
	Notification Details										

Description of Change:

Texas Instruments Incorporated is announcing an information only notification.

The product datasheet(s) is being updated as summarized below.

The following change history provides further details.



OPA838

SBOS867A - AUGUST 2017-REVISED FEBRUARY 2018

Ch	nanges from Original (August 2017) to Revision A	Page
	Added OPA837 to the Device Comparison table	4
	Changed Device Comparison table note	4
	Changed format of pin names in pinout drawings in Pin Configuration and Functions section	4
	Added DCK to pinout description in 6-pin SOT-23 and SC70 pinout drawing	4
•	Changed I/O column header to "TYPE" in Pin Configuration and Functions section	4
	Added table note to table to define pin types in Pin Configuration and Functions section	4
•	Added table note to Absolute Maximum Ratings table	5
•	Changed bandwidth for 0.1-dB flatness test condition from $V_{OUT} = 2 V_{PP}$ and $G = 10$ to $V_{OUT} = 200 \text{ mV}_{PP}$ and $G = 6$ in the Electrical Characteristics: $V_S = 5 \text{ V}$ table	6
•	Added values for V _{OH} and V _{OL} parameters at T _A = -40 to +125°C in Electrical Characteristics: V _S = 5 V table	7
•	Changed typical bandwidth for 0.1-dB flatness from 5 MHz to 9 MHz in Electrical Characteristics: $V_S = 3 \text{ V}$ table	8
•	Changed bandwidth for 0.1-dB flatness test conditions from $V_{OUT} = 2 V_{PP}$ and $G = 10$ to $V_{OUT} = 200 \text{ mV}_{PP}$ and $G = 6$ in Electrical Characteristics: $V_S = 3 V$ table	
	Added values for V _{OH} and V _{OL} parameters at T _A = -40 to +125°C in Electrical Characteristics: V _S = 3 V table	9
	Changed V _O test condition from 20 mV to 200 mV in Figure 5	10
•	Changed V _O test condition from 20 mV to 200 mV in Figure 6	10
•	Changed test conditions from V_{OUT} = 2 V_{PP} , R_F = 0 Ω , G = 1 V/V to R_F = 1 $k\Omega$, R_G = 200 Ω , R_L = 2 $k\Omega$, G = 6 V/V in Typical Characteristics: V_S = 3 V section	13
	Changed V _O test condition from 20 mV to 200 mV in Figure 23	
	Changed V _O test condition from 20 mV to 200 mV in Figure 24	
	Added condition statement to Typical Characteristics: Over Supply Range	16
•	Changed Y-axis label from "Disable and Vo (Bipolar supplies)" to "Disable and V _{OUT} (Bipolar Supplies, Volts)" in Figure 51	
	Changed Y-axis label from "PD and Output Voltages" to " Disable and V _{OUT} (Bipolar Supplies, Volts)" in Figure 52	17
•	Deleted 5-V supply and changed the Y-axis label of Figure 57	18

 Changed specification load value from 1-kΩ to 2-kΩ 	in Output Voltage Range section	121			
Changed first paragraph to correct power down logic in Power-Down Operation section					
 Changed image references in Power-Down Operation 	on section	21			
 Changed V1 value from 2.5 Ω to 2.5 V in Figure 64. 		22			
 Changed V2 value from 2.5 Ω to –2.5 V in Figure 64 		22			
 Changed V1 value from 2.5 Ω to 2.5 V, changed V2 	value from 2.5 Ω to –2.5 V, and	changed R _{OUT} to R _{LOAD} in			
Figure 66					
 Changed V_{OUT} input signal from ±.035 V_{OUT} to ±0.35 	V _{IN} in Figure 68	24			
 Changed V1 value from 4.5 Ω to 4.5 V in Figure 70. 		25			
Changed V _{EE} to ground in Figure 70					
 Changed V1 value from 3 Ω to 3 V in Figure 72 					
 Updated Single-Supply Op Amp Design Techniques 	application report link in Device	Functional Modes section 27			
 Changed "Cs" and "Cf" to "C_s" and "C_F" in Application 	on Information section	34			
 Updated Transimpedance Considerations for High-S 	Updated Transimpedance Considerations for High-Speed Amplifiers application report link in Detailed Design				
Procedure section	Procedure section.				
 Changed EVM guide link in Layout Guidelines section 	on				
The datasheet number will be changing.					
Device Family	Change From:	Change To:			
OPA838	SBOS867	SBOS867A			
UFA030	1 22 3 3 3 7	2233377			

These changes may be reviewed at the datasheet links provided.

http://www.ti.com/product/OPA838

Reason for Change:

To accurately reflect device characteristics.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

No anticipated impact. This is a specification change announcement only. There are no changes to the actual device.

Changes to product identification resulting from this PCN:

None.

Product Affected:

OPA838IDBVR	OPA838IDBVT	OPA838IDCKR	OPA838IDCKT
OPA838SIDCKR	OPA838SIDCKT		

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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